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List of reference symbols

- 1 semiconductor substrate
- 2 first trench
- 5 3 oxidized silicon layer
 - 4 aluminium-oxide layer
 - 5 horizontal regions
 - 6 second trench
 - 7 widened second trench
- 10 8 bottle structure
 - 9 first electrode
 - 10 dielectric layer
 - 11 conductive filling
 - 12 rugged polysilicon layer
- 15 13 first silicon nitride layer
 - 14 silicon nitride layer
 - 15 hardmask
 - 16 process window